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(71)Name of Applicant :

1)Chitkara University

Address of Applicant :Chitkara University, Chandigarh-Patiala National Highway, Village Jhansla, Rajpura, Punjab - 140401, India. Patiala -----

2)Chitkara Innovation Incubator Foundation

Name of Applicant : NA

Address of Applicant : NA

(72)Name of Inventor :

1)THAKUR, Diksha

Address of Applicant :Research Scholar, Department of Electronics and Communication Engineering, Chitkara University, Chandigarh-Patiala National Highway, Village Jhansla, Rajpura, Punjab - 140401, India. Patiala -----

2)SHARMA, Kulbhushan

Address of Applicant :Assistant Professor, Department of Electronics and Communication Engineering, Chitkara University, Chandigarh-Patiala National Highway, Village Jhansla, Rajpura, Punjab - 140401, India. Patiala -----

(57) Abstract :

An enhanced flipped source follower filter circuit for low-power consumption at low-voltage is disclosed. The circuit comprise MOS transistor M1. M1 is an input transistor and a current sink diode connected to output of transistor (M3). The circuit further comprises MOS transistor M2 which is shunt-shunt feedback transistor, a capacitor C1 and a capacitor C2, a current source transistor (M5) and a current source transistor (M6), the MOS transistor M3 as a current sink diode connected and diode connected output transistor, and MOS transistor M4 as a level shifter transistor. The circuit achieves a low cut-off frequency without increasing area overheads, and the diode connected MOS transistors provide unity-gain, low-current operation and lower power consumption

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